

## PALM INTRANET

Day: Monday Date: 11/14/2005

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## **Inventor Name Search Result**

Your Search was:

Last Name = BENSAHEL First Name = DANIEL

Application#	Patent#	Status	Date Filed	Title	Inventor Name
06042081	4263056	150	05/24/1979	METHOD FOR THE MANUFACTURE OF LIGHT EMITTING AND/OR PHOTODETECTIVE DIODES	BENSAHEL, DANIEL
06085948	4229237	150	10/18/1979	METHOD OF FABRICATION OF SEMICONDUCTOR COMPONENTS HAVING OPTOELECTRONIC CONVERSION PROPERTIES	BENSAHEL, DANIEL
06853906	4678538	250	04/21/1986	PROCESS FOR THE PRODUCTION OF AN INSULATING SUPPORT ON AN ORIENTED MONOCRYSTALLINE SILICON FILM WITH LOCALIZED DEFECTS	BENSAHEL, DANIEL
06882901	4725561	150	06/05/1986	PROCESS FOR THE PRODUCTION OF MUTUALLY ELECTRICALLY INSULATED MONOCRYSTALLINE SILICON ISLANDS USING LASER RECRYSTALLIZATION	BENSAHEL, DANIEL
07808745	5252181	150	12/17/1991	METHOD FOR CLEANING THE SURFACE OF A SUBSTRATE WITH PLASMA	BENSAHEL, DANIEL
07914380	Not Issued	161	07/15/1992	DEVICE FOR INJECTING A PRODUCT INTO AN ENCLOSED CHAMBER SUCH AS A REACTOR FOR MICROELECTRONICS	BENSAHEL, DANIEL
<u>08797511</u>	5876796	150	12/23/1996	PROCESS FOR SELECTIVELY DEPOSITING A REFRACTORY METAL SILICIDE ON SILICON, AND SILICON WAFER	BENSAHEL, DANIEL

7				METALLIZED USING THIS	
09217025	6117750	150	12/21/1998		BENSAHEL, DANIEL
09403356	6372581	150	10/18/1999	PROCESS FOR NITRIDING THE GATE OXIDE LAYER OF A SEMICONDUCTOR DEVICE AND DEVICE OBTAINED	BENSAHEL, DANIEL
09403442	6255149	150	10/19/1999	PROCESS FOR RESTRICTING INTERDIFFUSION IN A SEMICONDUCTOR DEVICE WITH COMPOSITE SI/SIGE GATE	BENSAHEL, DANIEL
09540188	6399502	150	03/31/2000	PROCESS FOR FABRICATING A PLANAR HETEROSTRUCTURE	BENSAHEL, DANIEL
09659913	6429098	150	09/11/2000	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM OR SILICON ON A SUBSTRATE OF SINGLE- CRYSTAL SILICON OR GERMANIUM, RESPECTIVELY, AND MULTILAYER PRODUCTS OBTAINED	BENSAHEL, DANIEL
09763532	6551698	150		METHOD FOR TREATING A SILICON SUBSTRATE, BY NITRIDING, TO FORM A THIN INSULATING LAYER	BENSAHEL, DANIEL
09786996	6537370	150			BENSAHEL, DANIEL
09921642	6596555	150		FORMING OF QUANTUM DOTS	BENSAHEL, DANIEL
10048719	6690027			METHOD FOR MAKING A DEVICE COMPRISING LAYERS OF PLANES OF QUANTUM DOTS	BENSAHEL, DANIEL
<u>10405075</u>	Not	95	03/31/2003	STRAINED-CHANNEL	BENSAHEL,

	Issued			ISOLATED-GATE FIELD EFFECT TRANSISTOR, PROCESS FOR MAKING SAME AND RESULTING INTEGRATED CIRCUIT	DANIEL
10614675	Not Issued	71	07/07/2003	Growth of a single-crystal region of a III-V compound on a single-crystal silicon substrate	BENSAHEL, DANIEL
10615259	6953736	150	07/09/2003	PROCESS FOR TRANSFERRING A LAYER OF STRAINED SEMICONDUCTOR MATERIAL	BENSAHEL, DANIEL
10744680	6969661	150	12/23/2003	METHOD FOR FORMING A LOCALIZED REGION OF A MATERIAL DIFFICULT TO ETCH	BENSAHEL, DANIEL
10815473	Not Issued	30	04/01/2004	Method of fabricating a semiconductor device comprising a gate dielectric made of high dielectric permittivity material	BENSAHEL, DANIEL
10816214	Not Issued	30	04/01/2004	Heteroatomic single-crystal layers	BENSAHEL, DANIEL
10882995	Not Issued	30	07/01/2004	Process for fabricating strained layers of silicon or of a silicon/germanium alloy	BENSAHEL, DANIEL
11165339	Not Issued	30	06/24/2005	Process for transferring a layer of strained semiconductor material	BENSAHEL, DANIEL
60445825	Not Issued	159	02/10/2003	Process for transferring a layer of strained semiconductor material	BENSAHEL, DANIEL
<u>60461656</u>	Not Issued	159	04/09/2003	Terahertz sources and detectors based on silicon and silicon germanium alloys and method of manufacture	BENSAHEL, DANIEL

Inventor Search Completed: No Records to Display.

Search Another:	Last Name	First Name	
	Inventor Repsahel	Daniel Searce	46 I
	{DCHOUNCE	Danier	<b></b>

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